## NSN 5961-00-044-3079

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-044-3079 **Inclosure Material:** Metal **Overall Length:** 0.380 inches **Overall Diameter:** 0.595 inches **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 3.0 gate trigger voltage, instantaneous **Current Rating Per Characteristic:** 80.00 amperes forward current, total rms watts **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npnp **Terminal Type And Quantity:** 1 pin and 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0